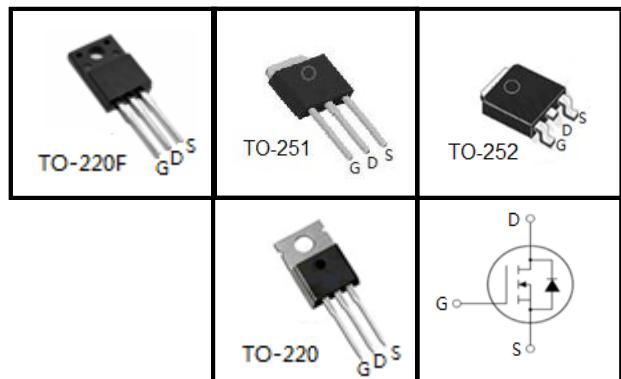


FEATURES

- Very low FOM $R_{DS(on)} \times Q_g$
- 100% avalanche tested
- RoHS compliant



APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)

Device Marking and Package Information				
Device	SP70R70	SP70R70	SP70R70	SP70R70
Package	TO-220	TO-220F	TO-251	TO-252
Marking	SP70R70P	SP70R70F	SP70R70U	SP70R70T

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Value		Unit
		TO-220, TO-251, TO-252	TO-220F	
Drain-Source Voltage ($V_{GS} = 0\text{V}$)	V_{DSS}	700		V
Continuous Drain Current	I_D	7		A
Pulsed Drain Current (note1)	I_{DM}	21		A
Gate-Source Voltage	V_{GSS}	± 30		V
Single Pulse Avalanche Energy (note2)	E_{AS}	162		mJ
Avalanche Current (note1)	I_{AR}	1.4		A
Repetitive Avalanche Energy (note1)	E_{AR}	0.2		mJ
Power Dissipation ($T_C = 25^\circ\text{C}$)	P_D	63	28	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	$-55\text{--}+150$		°C

Thermal Resistance				
Parameter	Symbol	Value		Unit
		TO-220, TO-251, TO-252	TO-220F	
Thermal Resistance, Junction-to-Case	R_{thJC}	2.0	4.5	°C/W
Thermal Resistance, Junction-to-Ambient	R_{thJA}	62	80	

Specifications $T_J = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_D = 250\mu\text{A}$	700	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}} = 700\text{V}, V_{\text{GS}} = 0\text{V}, T_J = 25^\circ\text{C}$	--	--	1	μA
		$V_{\text{DS}} = 700\text{V}, V_{\text{GS}} = 0\text{V}, T_J = 150^\circ\text{C}$	--	--	100	
Gate-Source Leakage	I_{GSS}	$V_{\text{GS}} = \pm 30\text{V}$	--	--	± 100	nA
Gate-Source Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = 250\mu\text{A}$	2.5	--	4.0	V
Drain-Source On-Resistance (Note3)	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 10\text{V}, I_D = 3\text{A}$	--	0.74	0.85	Ω
Forward Transconductance (Note3)	g_{fs}	$V_{\text{DS}} = 10\text{V}, I_D = 3\text{A}$	--	5	--	S
Dynamic						
Input Capacitance	C_{iss}	$V_{\text{GS}} = 0\text{V}, V_{\text{DS}} = 50\text{V}, f = 1.0\text{MHz}$	--	587	--	pF
Output Capacitance	C_{oss}		--	31	--	
Reverse Transfer Capacitance	C_{rss}		--	4	--	
Total Gate Charge	Q_g	$V_{\text{DD}} = 560\text{V}, I_D = 7\text{A}, V_{\text{GS}} = 10\text{V}$	--	14.5	--	nC
Gate-Source Charge	Q_{gs}		--	3	--	
Gate-Drain Charge	Q_{gd}		--	5.2	--	
Turn-on Delay Time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}} = 400\text{V}, I_D = 7\text{A}, R_G = 25\Omega$	--	39	--	ns
Turn-on Rise Time	t_r		--	25	--	
Turn-off Delay Time	$t_{\text{d}(\text{off})}$		--	100	--	
Turn-off Fall Time	t_f		--	18	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	$T_C = 25^\circ\text{C}$	--	--	6.3	A
Pulsed Diode Forward Current	I_{SM}		--	--	19	
Body Diode Voltage	V_{SD}	$T_J = 25^\circ\text{C}, I_{\text{SD}} = 7\text{A}, V_{\text{GS}} = 0\text{V}$	--	0.9	1.2	V
Reverse Recovery Time	t_{rr}	$V_R = 560\text{V}, I_F = I_S, dI_F/dt = 100\text{A}/\mu\text{s}$	--	250	--	ns
Reverse Recovery Charge	Q_{rr}		--	2.1	--	
Peak Reverse Recovery Current	I_{rrm}		--	16	--	A

Notes

- Repetitive Rating: Pulse Width limited by maximum junction temperature
- $I_{AS} = 1.4\text{A}, V_{\text{DD}} = 50\text{V}, R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
- Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 1\%$

Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics

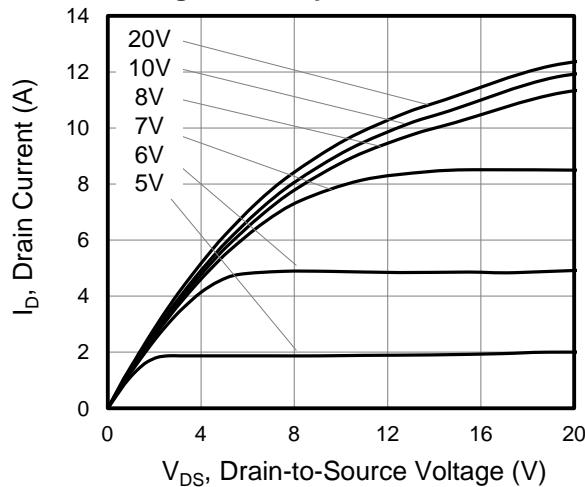


Figure 2. Transfer Characteristics

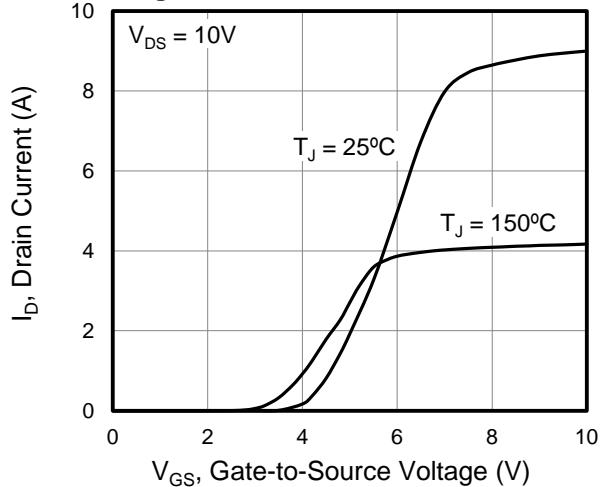


Figure 3. On-Resistance vs. Drain Current

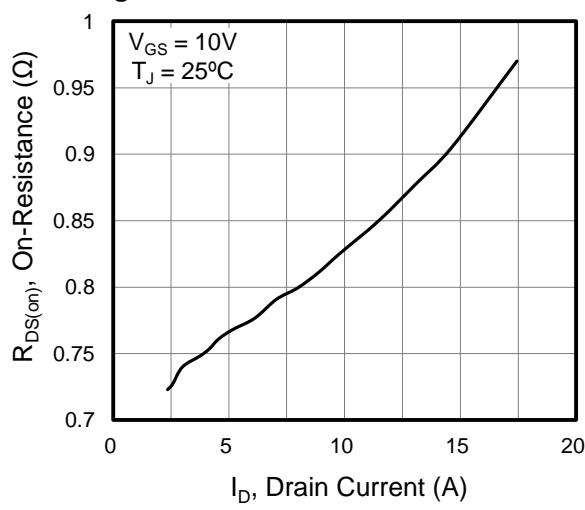


Figure 4. Capacitance

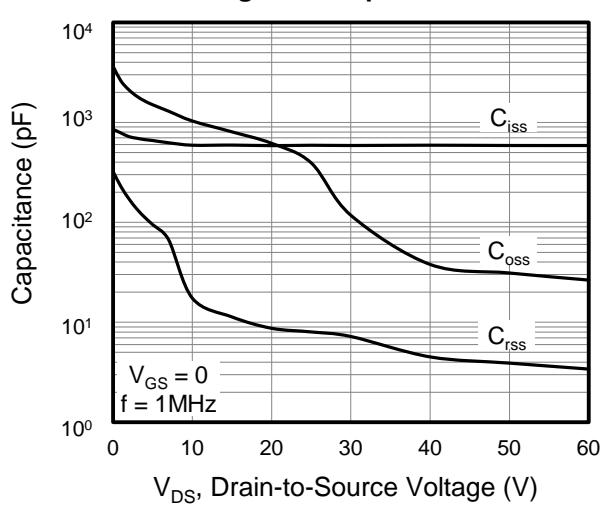


Figure 5. Gate Charge

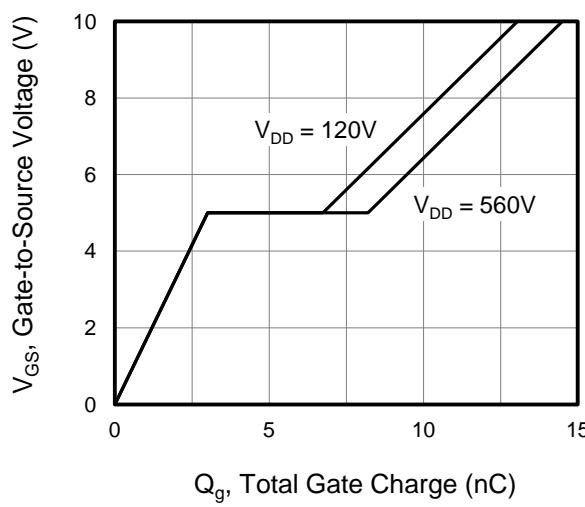
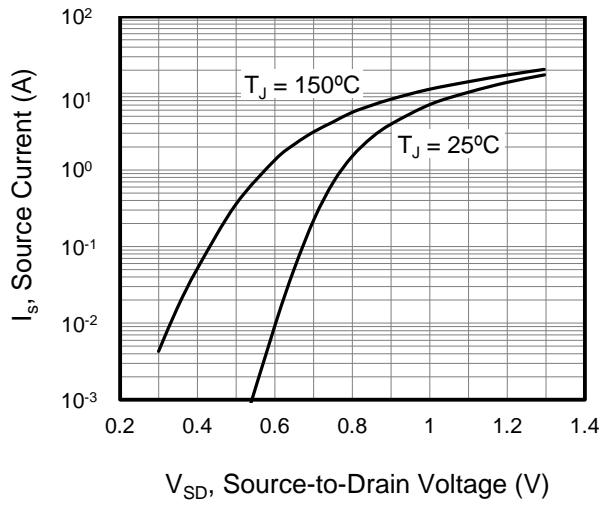
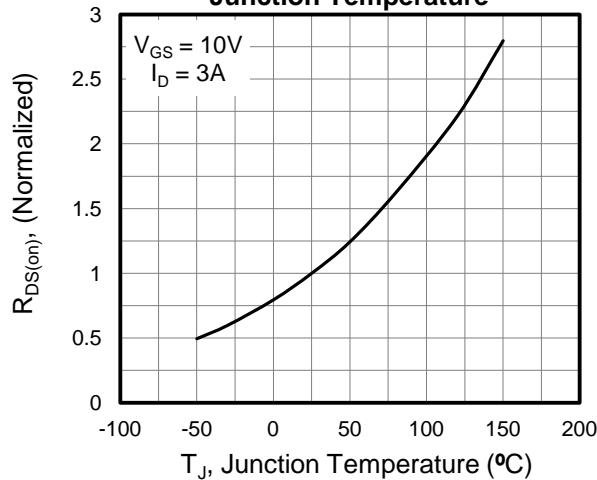


Figure 6. Body Diode Forward Voltage

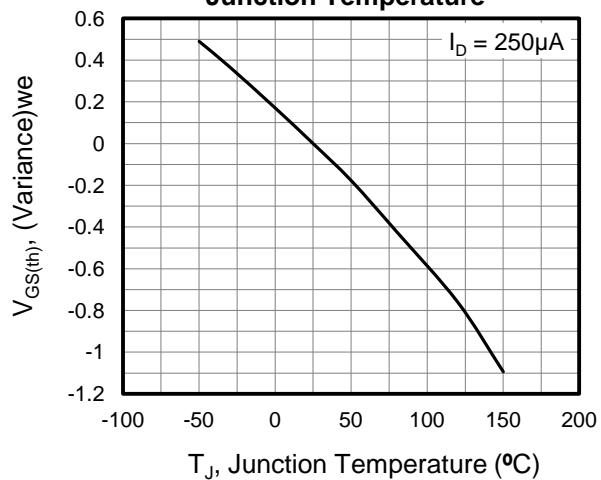


Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

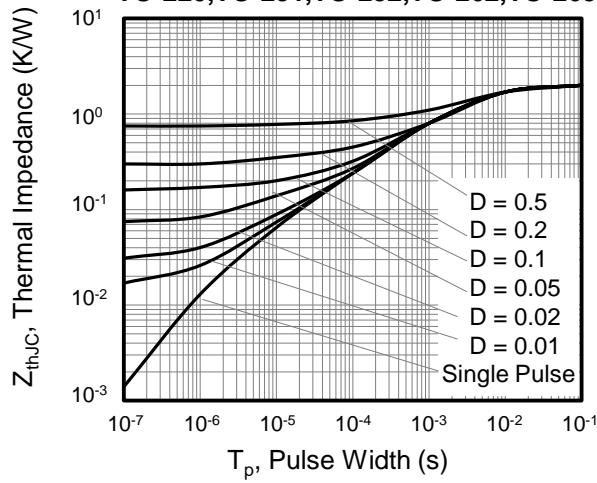
**Figure 7. On-Resistance vs.
Junction Temperature**



**Figure 8. Threshold Voltage vs.
Junction Temperature**



**Figure 9. Transient Thermal Impedance
TO-220, TO-251, TO-252, TO-262, TO-263**



**Figure 10. Transient Thermal Impedance
TO-220F**

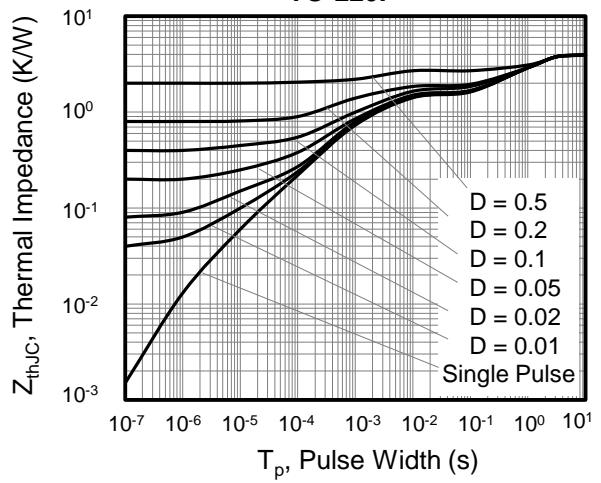
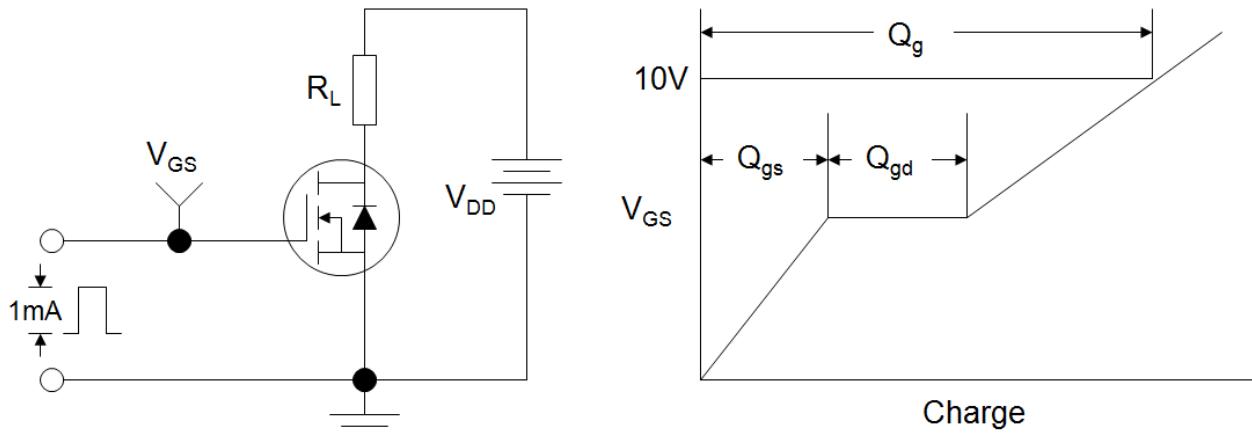
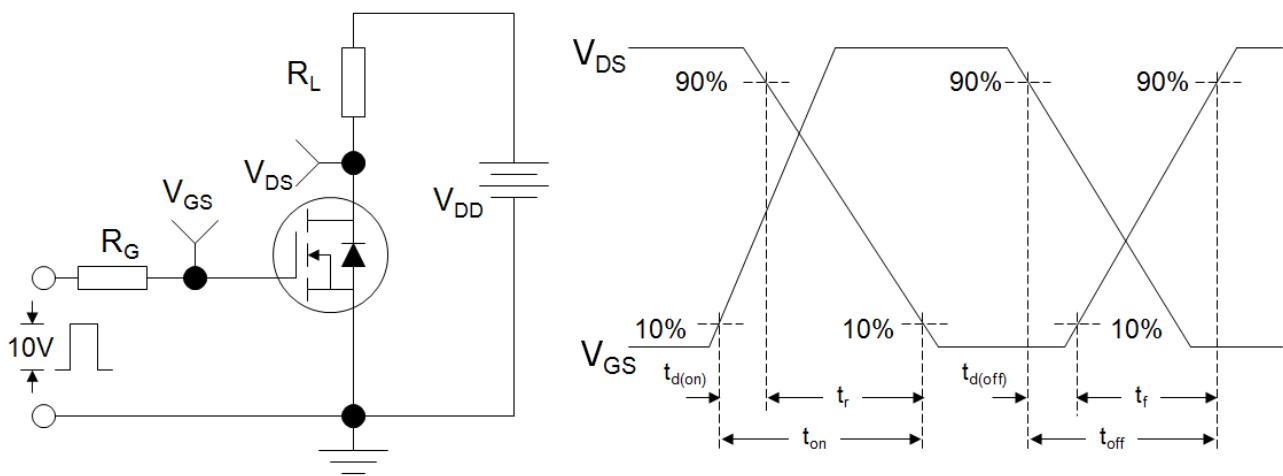
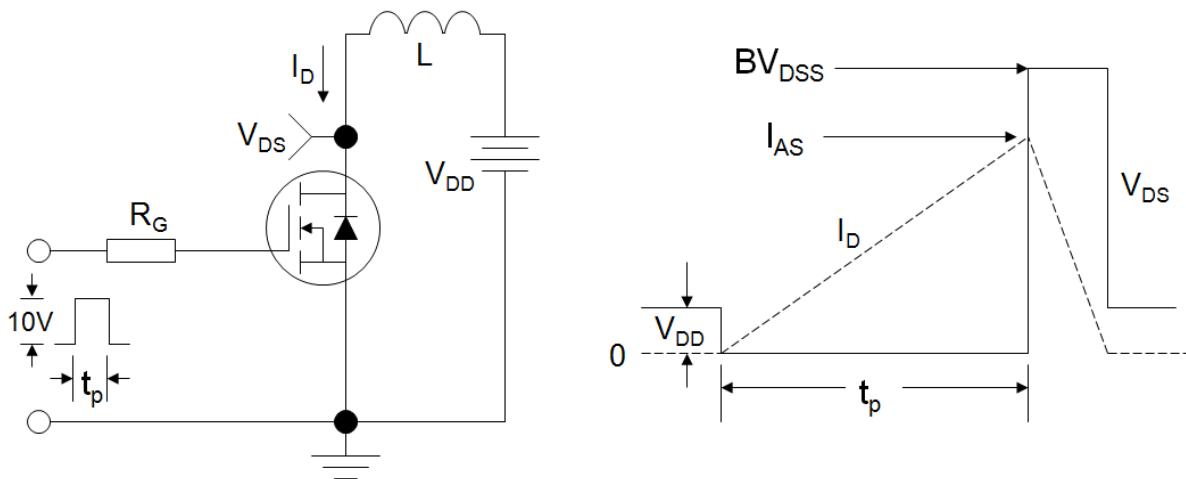
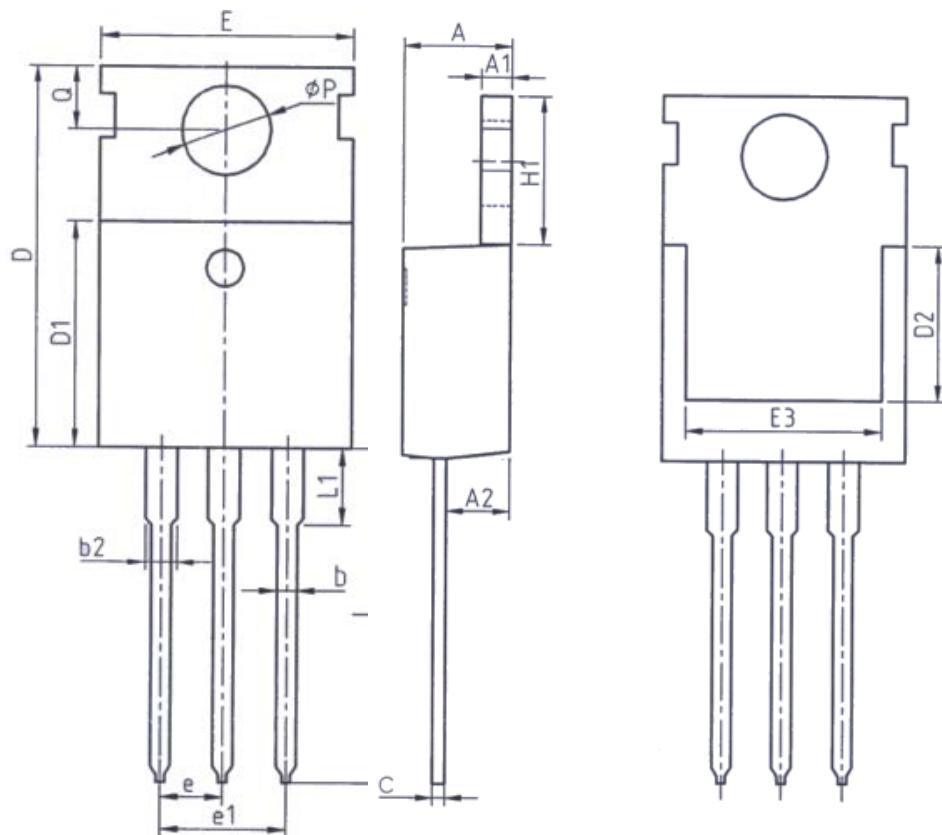


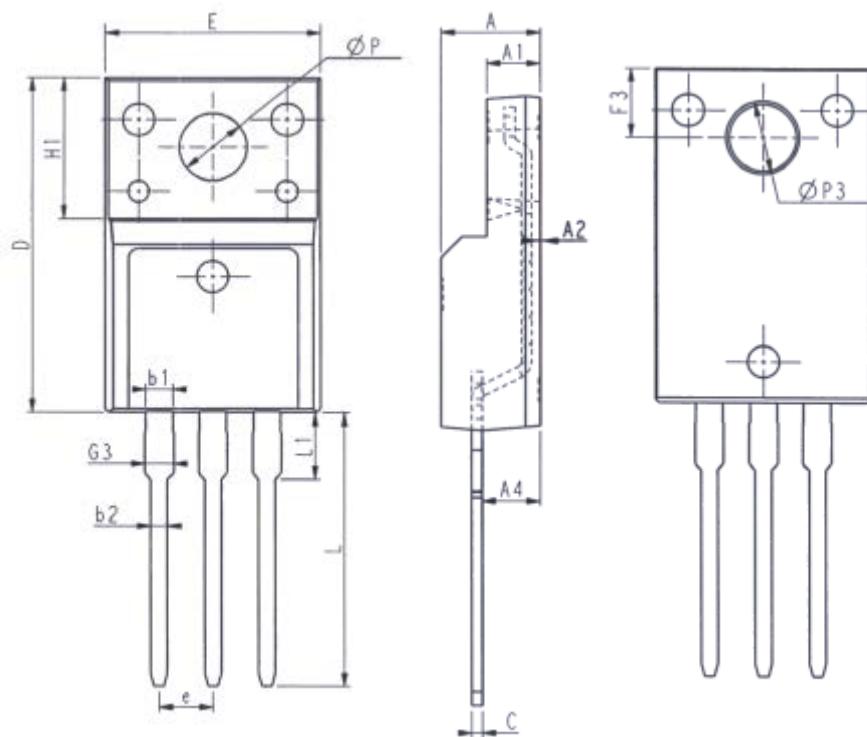
Figure A: Gate Charge Test Circuit and Waveform

Figure B: Resistive Switching Test Circuit and Waveform

Figure C: Unclamped Inductive Switching Test Circuit and Waveform


TO-220


Unit: mm		
Symbol	Min.	Max.
A	4.37	4.77
A1	1.25	1.45
A2	2.20	2.60
b	0.70	0.95
b2	1.17	1.47
c	0.40	0.65
D	15.10	16.10
D1	8.80	9.40
D2	5.50	-

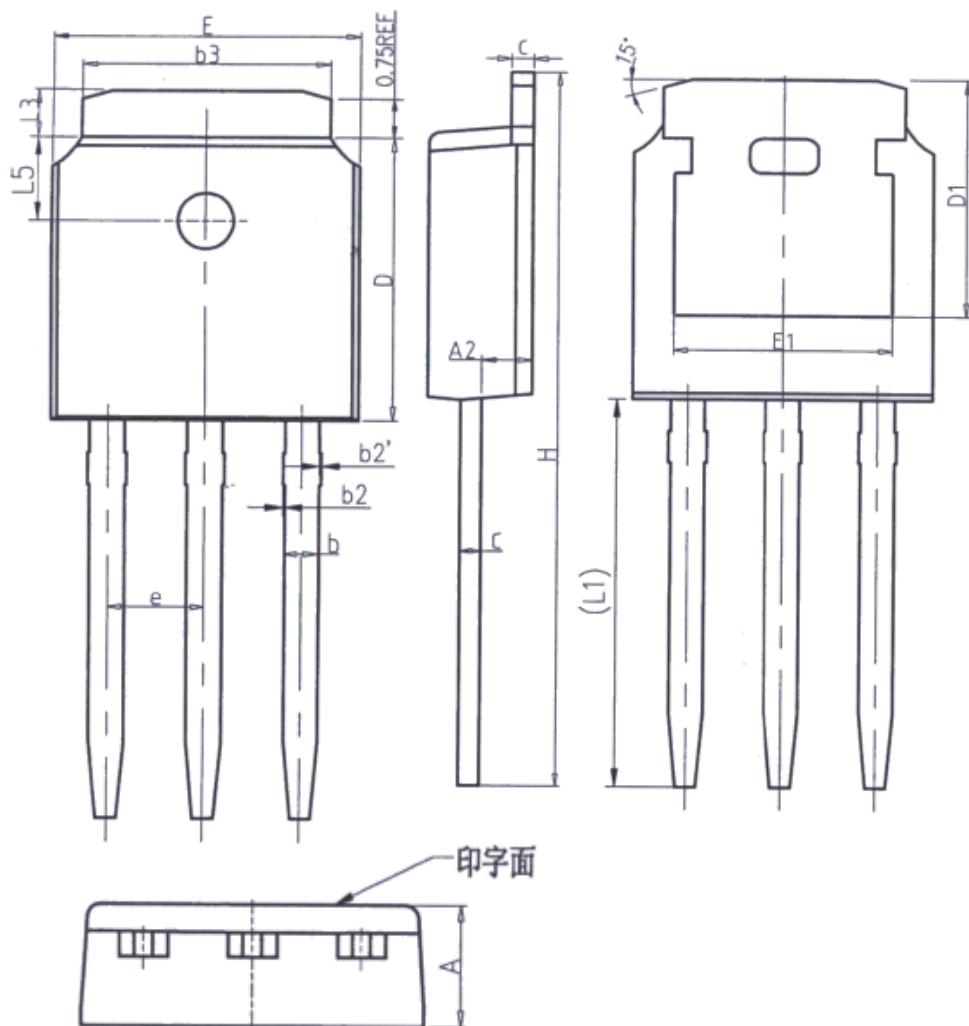
Unit: mm		
Symbol	Min.	Max.
E	9.70	10.30
E3	7.00	-
e	2.54BSC	
e1	5.08BSC	
H1	6.25	6.85
L	12.75	13.80
L1	-	3.40
P	3.40	3.80
Q	2.60	3.00

TO-220F



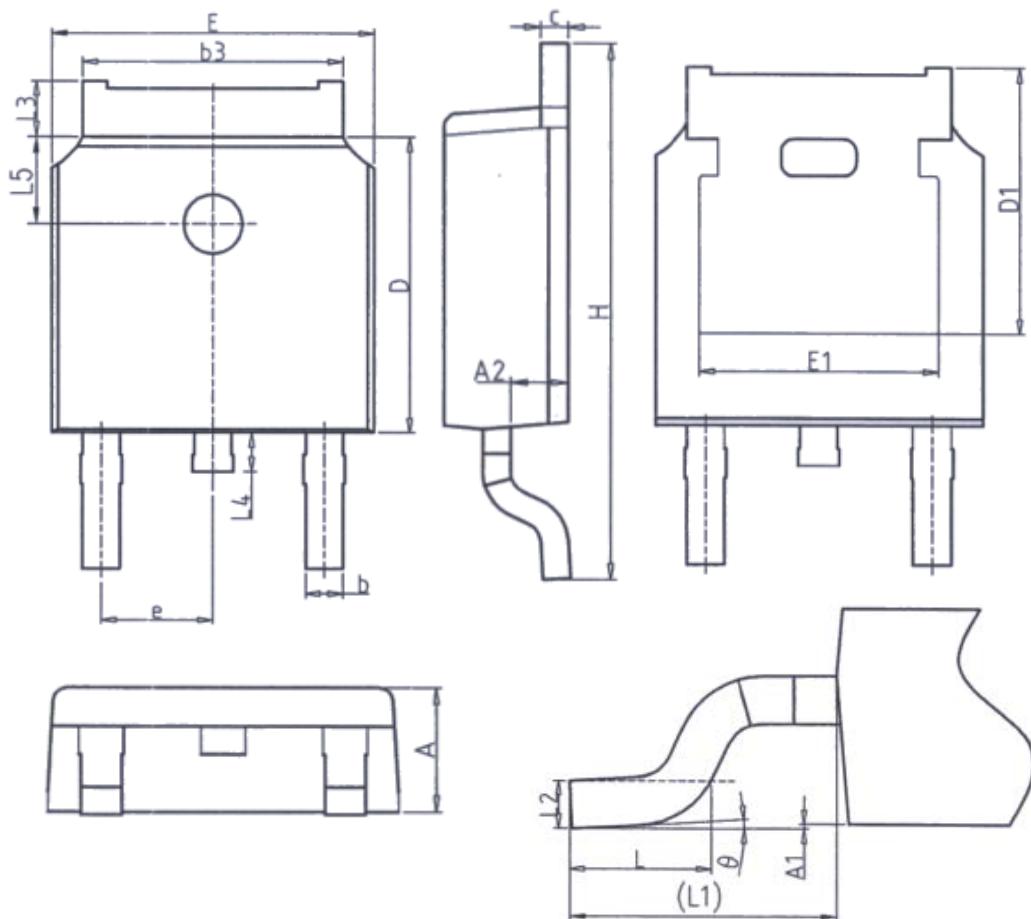
Unit: mm		
Symbol	Min.	Max.
E	9.96	10.36
A	4.50	4.90
A1	2.34	2.74
A2	0.30	0.60
A4	2.56	2.96
c	0.40	0.65
D	15.57	16.17
H1	6.70REF	
e	2.54BSC	

Unit: mm		
Symbol	Min.	Max.
L	12.68	13.28
L1	2.93	3.13
P	3.03	3.38
P3	3.15	3.65
F3	3.15	3.45
G3	1.25	1.55
b1	1.18	1.43
b2	0.70	0.95

TO-251


Unit: mm		
Symbol	Min.	Max.
A	2.20	2.40
A2	0.97	1.17
b	0.68	0.90
b2	0.00	0.10
b2'	0.00	0.10
b3	5.20	5.50
c	0.43	0.63
D	5.98	6.22

Unit: mm		
Symbol	Min.	Max.
D1	5.30REF	
E	6.40	6.80
E1	4.63	-
e	2.286BSC	
H	16.22	16.82
L1	9.15	9.65
L3	0.88	1.28
L5	1.65	1.95

TO-252


Unit: mm		
Symbol	Min.	Max.
A	2.20	2.40
A1	0.00	0.20
A2	0.97	1.17
b	0.68	0.90
b3	5.20	5.50
c	0.43	0.63
D	5.98	6.22
D1	5.30REF	
E	6.40	6.80
E1	4.63	-

Unit: mm		
Symbol	Min.	Max.
e	2.286BSC	
H	9.40	10.50
L	1.38	1.75
L1	2.90REF	
L2	0.51BSC	
L3	0.88	1.28
L4	-	1.00
L5	1.65	1.95
theta	0°	8°